

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A semiconductor device comprising:

a first insulating film formed over a semiconductor substrate;

a capacitor constructed by forming a lower electrode, a dielectric film, and an upper electrode sequentially on the first insulating film;

a first capacitor protection insulating film covering the dielectric film and the upper electrode; a second capacitor protection insulating film formed on the first capacitor protection insulating film;

a second capacitor protection insulating film formed on the first capacitor protection insulating film; ~~and~~

a second insulating film formed on the first capacitor protection insulating film; ~~for covering the capacitor; and~~

a first-layer metal wiring formed on the second insulating film and connected electrically to the upper electrode by a plug extending through a contact hole in the second insulating film, the second capacitor protection insulating film and the first capacitor protection insulating film,

wherein an amount of carbon contained in the second capacitor protection insulating film is

larger than an amount of carbon contained in the second insulating film.

Claim 2 (Original): A semiconductor device according to claim 1, wherein the second capacitor protection insulating film is a silicon oxide film.

Claim 3 (Original): A semiconductor device according to claim 1, wherein the second insulating film is a silicon oxide film.

Claim 4 (Original): A semiconductor device according to claim 1, wherein the first capacitor protection insulating film is made of any one of alumina, PLZT, PZT, titanium oxide, aluminum nitride, silicon nitride, and silicon nitride oxide.

Claim 5 (Original): A semiconductor device according to claim 1, wherein the dielectric film is made of any one of PZT material and bismuth material.

Claim 6 (Original): A semiconductor device according to claim 1, wherein a hole reaching the upper electrode is formed in the capacitor protection insulating film, the second capacitor protection insulating film, and the second insulating film, and a wiring that is electrically connected to the upper electrode via the hole is formed on the second insulating film.

Claims 7 - 20 (Canceled)

Claim 21 (New): A semiconductor device comprising:

a first insulating film formed over a semiconductor substrate;

a capacitor constructed by forming a lower electrode, a dielectric film, and an upper electrode sequentially on the first insulating film;

a first capacitor protection insulating film covering the upper surface of the upper electrode and the aspect of the upper electrode and the dielectric film;

a second capacitor protection insulating film formed on the first capacitor protection insulating film; and

a second insulating film formed, in its entirety, directly on the second capacitor protection insulating film.

Claim 22 (New): A semiconductor device comprising:

a first insulating film formed over a semiconductor substrate;

a capacitor constructed by forming a lower electrode, a dielectric film, and an upper electrode sequentially on the first insulating film;

a first capacitor protection insulating film covering the dielectric film and the upper electrode;

a second capacitor protection insulating film formed on the first capacitor protection insulating film;

a second capacitor protection insulating film formed on the first capacitor protection insulating film;

a second insulating film formed on the first capacitor protection insulating film; and

a first-layer metal wiring formed on the second insulating film and connected electrically to the upper electrode by a plug extending through a contact hole in the second insulating film.

Claim 23 (New): A semiconductor device according to claim 22, wherein the first-layer metal wiring is formed on the second insulating film and connected electrically to the upper electrode by the plug extending through the contact hole in the second insulating film, the second capacitor protection insulating film and the first capacitor protection insulating film.